## Low-Voltage 1.8/2.5/3.3V 16-Bit Buffer

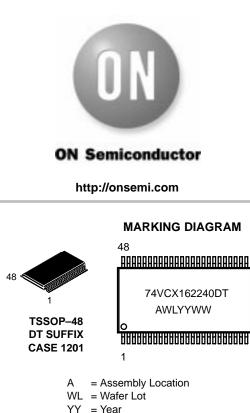
# With 26 $\Omega$ Series Resistors 3.6 V–Tolerant Inputs and Outputs (3–State, Inverting)

The 74VCX162240 is an advanced performance, inverting 16–bit buffer. It is designed for very high–speed, very low–power operation in 1.8 V, 2.5 V or 3.3 V systems.

When operating at 2.5 V (or 1.8 V) the part is designed to tolerate voltages it may encounter on either inputs or outputs when interfacing to 3.3 V busses. It is guaranteed to be over-voltage tolerant to 3.6 V.

The 74VCX162240 is nibble controlled with each nibble functioning identically, but independently. It is designed with 26  $\Omega$ series resistors in each of the outputs to reduce noise. The control pins may be tied together to obtain full 16-bit operation. The 3-state outputs are controlled by an Output Enable ( $\overline{OEn}$ ) input for each nibble. When  $\overline{OEn}$  is LOW, the outputs are on. When  $\overline{OEn}$  is HIGH, the outputs are in the high impedance state.

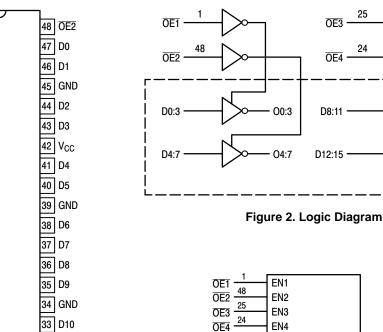
- Designed for Low Voltage Operation:  $V_{CC} = 1.65-3.6 \text{ V}$
- 3.6 V Tolerant Inputs and Outputs
- High Speed Operation: 3.3 ns max for 3.0 to 3.6 V
  3.8 ns max for 2.3 to 2.7 V
  7.6 ns max for 1.65 to 1.95 V
- Static Drive: ±12 mA Drive at 3.0 V ±8 mA Drive at 2.3 V ±3 mA Drive at 1.65 V
- Supports Live Insertion and Withdrawal
- $I_{OFF}$  Specification Guarantees High Impedance When  $V_{CC} = 0$  V
- Near Zero Static Supply Current in All Three Logic States (20 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±300 mA @ 125°C
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



**ORDERING INFORMATION** 

WW = Work Week

Device	Package	Shipping
74VCX162240DT	TSSOP	39 / Rail
74VCX162240DTR	TSSOP	2500 / Reel



25				
DE3	EN3			
0E4	EN4			
064				]
D0-47	┍┸──	1	1 🕅	<u>2</u> 00
D1 46				3 01
D2 44	<u> </u>			5 02
D2 43		1	2 \(\nabla\)	<u>6</u> 03
D4	<u> </u>			<u>8</u> 04
	<u> </u>			<u> </u>
D6-30	<u> </u>			<u>11</u> 06
D7 3/	<u> </u>	1	3 \(\nabla\)	12 07
D8-30	<u> </u>		0 1	13 08
D9 <u>35</u>				<u>14</u> 09
D10 33				16 010
D10 32	<u> </u>	1	4 V	<u>17</u> 010
D112 30 D12 29	<u> </u>		4 V	19 012
D12 D13 27	┣───			20 012 20 013
D13 D14 26	┣───			22 013
D14	└───			23 014
D15 <u>26</u>	1			015

08:11

012:15

One of Four

V<sub>CC</sub> 18 31 V<sub>CC</sub> 012 19 30 D12 013 20 29 D13 GND 21 28 GND 014 22 27 D14 015 23 26 D15 0E4 24 25 OE3 Figure 1. 48–Lead Pinout (Top View)

32 D11

#### **PIN NAMES**

0E1 1

00 2

01 3

GND 4

02 5

03 6

04 8

05 9

GND 10

08 13

09 14

GND 15

010 16

011 17

V<sub>CC</sub> 7

Ο

Pins	Function
OEn	Output Enable Inputs
D0–D15	Inputs
O0–O15	Outputs

OE1	D0:3	O0:3	OE2	D4:7	04:7	OE3	D8:11	O8:11	OE4	D12:15	012:15
L	L	L	L	L	L	L	L	L	L	L	L
L	Н	Н	L	Н	Н	L	Н	Н	L	Н	Н
н	Х	Z	н	Х	Z	н	Х	Z	Н	Х	Z

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions Are Acceptable, for  $I_{CC}$  reasons, DO NOT FLOAT Inputs

## **ABSOLUTE MAXIMUM RATINGS\***

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +4.6$		V
Vo	DC Output Voltage	$-0.5 \le V_0 \le +4.6$	Output in 3-State	V
		$-0.5 \leq V_O \leq V_{CC} + 0.5$	Note 1.; Outputs Active	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	$V_{O} > V_{CC}$	mA
IO	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

\* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

1. I<sub>O</sub> absolute maximum rating must be observed.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Тур	Max	Unit
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only	1.65 1.2	3.3	3.6 3.6	V
VI	Input Voltage		-0.3		3.6	V
V <sub>O</sub>	Output Voltage (Active State) (3–State)		0 0		V <sub>CC</sub> 3.6	V
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 3.0V – 3.6V				-12	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> = 3.0V – 3.6V				12	mA
I <sub>OH</sub>	HIGH Level Output Current, $V_{CC} = 2.3V - 2.7V$				-8	mA
I <sub>OL</sub>	LOW Level Output Current, $V_{CC} = 2.3V - 2.7V$				8	mA
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> = 1.65V – 1.95V				-3	mA
I <sub>OL</sub>	LOW Level Output Current, $V_{CC} = 1.65V - 1.95V$				3	mA
T <sub>A</sub>	Operating Free–Air Temperature		-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, VIN from 0.8V to	2.0V, V <sub>CC</sub> = 3.0V	0		10	ns/V

### DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = -40°0	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
VIH	HIGH Level Input Voltage (Note 2.)	$1.65V \le V_{CC} < 2.3V$	0.65 x V <sub>CC</sub>		V
		$2.3V \le V_{CC} \le 2.7V$	1.6		
		$2.7V < V_{CC} \le 3.6V$	2.0		
V <sub>IL</sub>	LOW Level Input Voltage (Note 2.)	$1.65V \le V_{CC} < 2.3V$		0.35 x V <sub>CC</sub>	V
		$2.3V \le V_{CC} \le 2.7V$		0.7	
		$2.7V < V_{CC} \le 3.6V$		0.8	
V <sub>OH</sub>	HIGH Level Output Voltage	$1.65V \le V_{CC} \le 3.6V; I_{OH} = -100\mu A$	V <sub>CC</sub> - 0.2		V
		V <sub>CC</sub> = 1.65V; I <sub>OH</sub> = -3mA	1.25		
		V <sub>CC</sub> = 2.3V; I <sub>OH</sub> = -4mA	2.0		
		V <sub>CC</sub> = 2.3V; I <sub>OH</sub> = -6mA	1.8		
		V <sub>CC</sub> = 2.3V; I <sub>OH</sub> = -8mA	1.7		
		V <sub>CC</sub> = 2.7V; I <sub>OH</sub> = -6mA	2.2		
		V <sub>CC</sub> = 3.0V; I <sub>OH</sub> = -8mA	2.4		
		V <sub>CC</sub> = 3.0V; I <sub>OH</sub> = -12mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	$1.65V \le V_{CC} \le 3.6V; I_{OL} = 100\mu A$		0.2	V
		V <sub>CC</sub> = 1.65V; I <sub>OL</sub> = 3mA		0.3	
		V <sub>CC</sub> = 2.3V; I <sub>OL</sub> = 6mA		0.4	
		V <sub>CC</sub> = 2.3V; I <sub>OL</sub> = 8mA		0.6	
		V <sub>CC</sub> = 2.7V; I <sub>OL</sub> = 6mA		0.4	
		V <sub>CC</sub> = 3.0V; I <sub>OL</sub> = 8mA		0.55	
		V <sub>CC</sub> = 3.0V; I <sub>OL</sub> = 12mA		0.8	
l <sub>l</sub>	Input Leakage Current	$1.65 \text{V} \leq \text{V}_{CC} \leq 3.6 \text{V}; \ 0 \text{V} \leq \text{V}_{I} \leq 3.6 \text{V}$		±5.0	μA
I <sub>OZ</sub>	3-State Output Current	$\begin{array}{c} 1.65 \text{V} \leq \text{V}_{CC} \leq 3.6 \text{V}; \ 0 \text{V} \leq \text{V}_{O} \leq 3.6 \text{V}; \\ \text{V}_{I} = \text{V}_{IH} \ \text{or} \ \text{V}_{IL} \end{array}$		±10	μA
I <sub>OFF</sub>	Power–Off Leakage Current	$V_{CC} = 0V; V_1 \text{ or } V_O = 3.6V$		10	μA
I <sub>CC</sub>	Quiescent Supply Current (Note 3.)	$1.65V \le V_{CC} \le 3.6V; V_I = GND \text{ or } V_{CC}$		20	μA
		$1.65V \le V_{CC} \le 3.6V; \ 3.6V \le V_I, \ V_O \le 3.6V$		±20	μA
∆l <sub>CC</sub>	Increase in I <sub>CC</sub> per Input	$2.7V < V_{CC} \le 3.6V; V_{IH} = V_{CC} - 0.6V$		750	μA

2. These values of  $V_I$  are used to test DC electrical characteristics only.

3. Outputs disabled or 3-state only.

AC CHARACTERISTICS (Note 4.;  $t_R = t_F = 2.0ns$ ;  $C_L = 30pF$ ;  $R_L = 500\Omega$ )

					Li	mits			
					T <sub>A</sub> = -40°	℃ to +85°C			
			V <sub>CC</sub> = 3.0	)V to 3.6V	V <sub>CC</sub> = 2.3	SV to 2.7V	V <sub>CC</sub> = 1.6	5 to 1.95V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Мах	Unit
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Input to Output	1	0.8 0.8	3.3 3.3	1.0 1.0	3.8 3.8	1.5 1.5	7.6 7.6	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	2	0.8 0.8	3.8 3.8	1.0 1.0	5.1 5.1	1.5 1.5	9.8 9.8	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time From High and Low Level	2	0.8 0.8	3.6 3.6	1.0 1.0	4.0 4.0	1.5 1.5	7.2 7.2	ns
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 5.)			0.5 0.5		0.5 0.5		0.75 0.75	ns

4. For  $C_L = 50$  pF, add approximately 300 ps to the AC maximum specification.

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t<sub>OSHL</sub>) or LOW–to–HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

### **DYNAMIC SWITCHING CHARACTERISTICS**

			T <sub>A</sub> = +25°C	
Symbol	Characteristic	Condition	Тур	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage	$V_{CC}$ = 1.8V, $C_L$ = 30pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0V	0.15	V
	(Note 6.)	$V_{CC}$ = 2.5V, $C_L$ = 30pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0V	0.25	
		$V_{CC} = 3.3 \text{V},  \text{C}_{\text{L}} = 30 \text{pF},  \text{V}_{\text{IH}} = \text{V}_{CC},  \text{V}_{\text{IL}} = 0 \text{V}$	0.35	1
V <sub>OLV</sub>	Dynamic LOW Valley Voltage	$V_{CC}$ = 1.8V, $C_L$ = 30pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0V	-0.15	V
	(Note 6.)	$V_{CC} = 2.5 \text{V},  \text{C}_{\text{L}} = 30 \text{p}\text{F},  \text{V}_{\text{IH}} = \text{V}_{CC},  \text{V}_{\text{IL}} = 0 \text{V}$	-0.25	
		$V_{CC} = 3.3$ V, $C_L = 30$ pF, $V_{IH} = V_{CC}$ , $V_{IL} = 0$ V	-0.35	1
V <sub>OHV</sub>	Dynamic HIGH Valley Voltage	$V_{CC}$ = 1.8V, $C_L$ = 30pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0V	1.55	V
	(Note 7.)	$V_{CC}$ = 2.5V, $C_L$ = 30pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0V	2.05	
		$V_{CC}$ = 3.3V, $C_L$ = 30pF, $V_{IH}$ = $V_{CC}$ , $V_{IL}$ = 0V	2.65	]

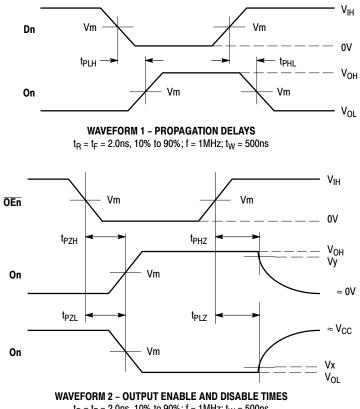
6. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state. 7. Number of outputs defined as "n". Measured with "n–1" outputs switching from HIGH-to–LOW or LOW-to–HIGH. The remaining output is

measured in the HIGH state.

#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	Note 8.	6	pF
C <sub>OUT</sub>	Output Capacitance	Note 8.	7	pF
C <sub>PD</sub>	Power Dissipation Capacitance	Note 8., 10MHz	20	pF

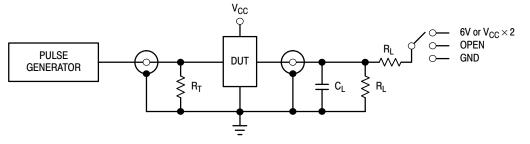
8.  $V_{CC}$  = 1.8, 2.5 or 3.3V;  $V_{I}$  = 0V or  $V_{CC}$ .



 $t_{R}$  =  $t_{F}$  = 2.0ns, 10% to 90%; f = 1MHz;  $t_{W}$  = 500ns

Figure 3. AC Waveforms

	V <sub>CC</sub>				
Symbol	3.3V ±0.3V	2.5V ±0.2V	1.8V ±0.15V		
V <sub>IH</sub>	2.7V	V <sub>CC</sub>	V <sub>CC</sub>		
V <sub>m</sub>	1.5V	V <sub>CC</sub> /2	V <sub>CC</sub> /2		
V <sub>x</sub>	V <sub>OL</sub> + 0.3V	V <sub>OL</sub> + 0.15V	V <sub>OL</sub> + 0.15V		
Vy	V <sub>OH</sub> – 0.3V	V <sub>OH</sub> – 0.15V	V <sub>OH</sub> – 0.15V		

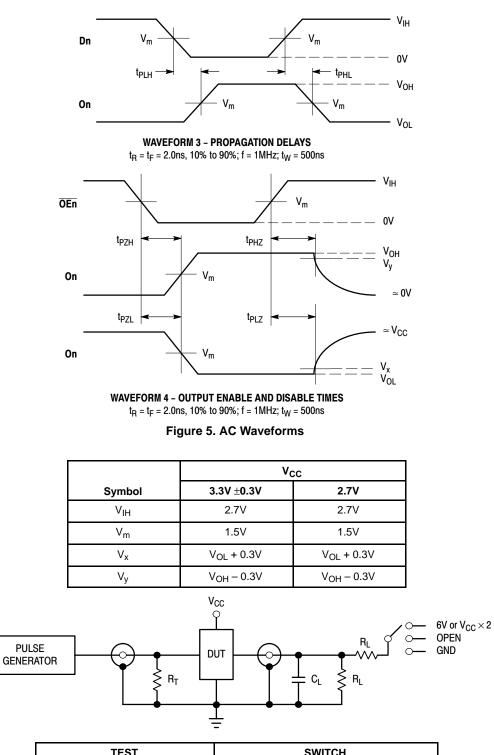


TEST	SWITCH
tPLH, tPHL	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	6V at V <sub>CC</sub> = $3.3 \pm 0.3$ V; V <sub>CC</sub> × 2 at V <sub>CC</sub> = $2.5 \pm 0.2$ V; $1.8 \pm 0.15$ V
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

 $C_L$  = 30pF or equivalent (Includes jig and probe capacitance)  $R_L$  = 500 $\Omega$  or equivalent

 $R_T = Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

Figure 4. Test Circuit



TEST	SWITCH			
t <sub>PLH</sub> , t <sub>PHL</sub>	Open			
t <sub>PZL</sub> , t <sub>PLZ</sub>	6V at V <sub>CC</sub> = $3.3 \pm 0.3$ V; V <sub>CC</sub> × 2 at V <sub>CC</sub> = $2.5 \pm 0.2$ V; 1.8 ±0.15V			
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND			

 $C_L$  = 50pF or equivalent (Includes jig and probe capacitance)

 $R_{L} = 500\Omega$  or equivalent

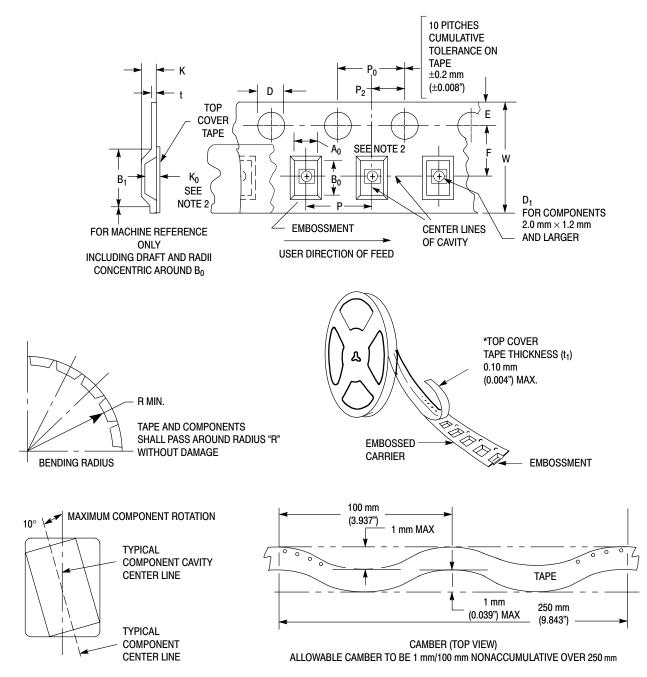
 $R_T = Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

Figure 6. Test Circuit

## AC CHARACTERISTICS ( $t_R = t_F = 2.0ns$ ; $C_L = 50pF$ ; $R_L = 500\Omega$ )

			Limits T <sub>A</sub> = -40°C to +85°C				-
			V <sub>CC</sub> = 3.0	)V to 3.6V	V <sub>CC</sub> =	= 2.7V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Input to Output	3	1.0 1.0	4.2 4.2		4.7 4.7	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	4	1.0 1.0	5.6 5.6		6.7 6.7	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time From High and Low Level	4	1.0 1.0	5.5 5.5		5.7 5.7	ns
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 9.)			0.5 0.5		0.5 0.5	ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t<sub>OSHL</sub>) or LOW–to–HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.





Tape Size	B <sub>1</sub> Max	D	D <sub>1</sub>	Е	F	к	Р	P <sub>0</sub>	P <sub>2</sub>	R	т	w
24mm	20.1mm (0.791")	1.5 + 0.1mm -0.0 (0.059 +0.004" -0.0)	1.5mm Min (0.060")	1.75 ±0.1 mm (0.069 ±0.004")	11.5 ±0.10 mm (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 ±0.1 mm (0.63 ±0.004")	4.0 ±0.1 mm (0.157 ±0.004")	2.0 ±0.1 mm (0.079 ±0.004")	30 mm (1.18")	0.6 mm (0.024")	24.3 mm (0.957")

#### EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

1. Metric Dimensions Govern-English are in parentheses for reference only.

 A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

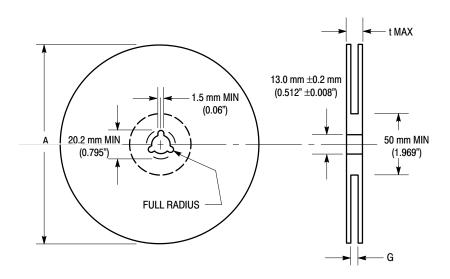
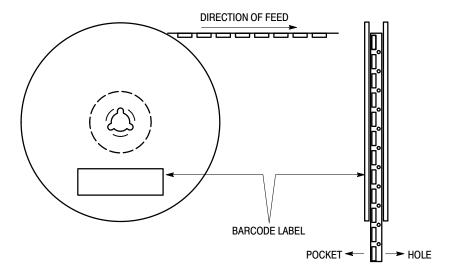


Figure 8. Reel Dimensions

### **REEL DIMENSIONS**

Tape Size	A Max	G	t Max
24 mm	360 mm	24.4 mm + 2.0 mm, -0.0	30.4 mm
	(14.173")	(0.961" + 0.078", -0.00)	(1.197")





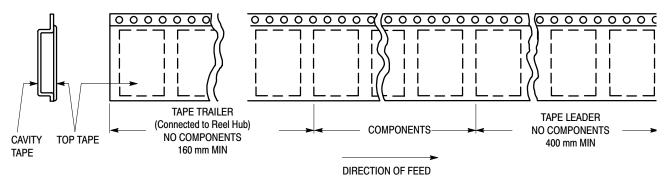
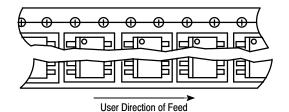
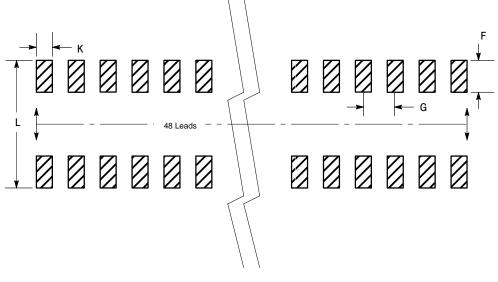


Figure 10. Tape Ends for Finished Goods



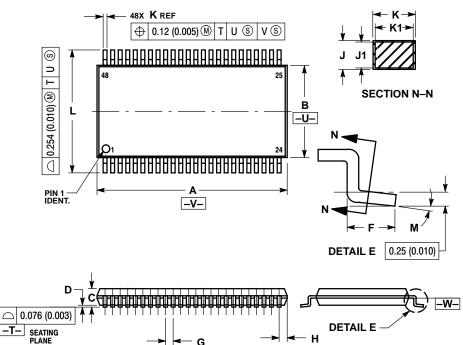




Package Footprint

#### PACKAGE DIMENSIONS

TSSOP DT SUFFIX CASE 1201-01 ISSUE A



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS
- SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR 4
- PROTRUSION R DOES NOT INCLODE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	12.40	12.60	0.488	0.496	
В	6.00	6.20	0.236	0.244	
C		1.10		0.043	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.50	BSC	0.0197 BSC		
н	0.37		0.015		
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.17	0.27	0.007	0.011	
K1	0.17	0.23	0.007	0.009	
L	7.95	8.25	0.313	0.325	
М	0 °	8 °	0 °	8 °	

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